

ABSTRACT OF THE DISCLOSURE

Provided are a method of manufacturing a semiconductor, a nonvolatile semiconductor memory device and a method of

5 manufacturing the same, wherein: the memory device has a plurality of memory cells; a buried diffusion layer serves as a signal line; and, a buried diffusion layer disposed adjacent to each of opposite end portions of a lower floating gate is free from variations in width resulted from misalignment occurring in an optical aligner.

10 In the memory device, for example: the floating gate is formed in an active region of a P-type semiconductor substrate through a gate oxide film; an N-type drain region and an N-type source region are formed in opposite end portions of the floating gate; and, a pair of device isolation shielding electrode extends in parallel with
15 the floating gate outside both the drain region and the source region to cover adjacent ones of the memory cells.